

BU508AF

BU508AF Information

	Part Number	BU508AF
www.heisenar.com	Manufacturer	STMicroelectronics
	Category	Discrete Semiconductor Products Transistors - Bipolar (BJT) - Single
	Description	TRANS NPN 700V 8A ISOWATT218FX
	Package	ISOWATT218FX
		For the pricing/inventory/lead time, please contact
For Reference Only		us Website: https://www.heisener.com E-mail: salesdept@heisener.com



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BU508AF Specifications

Manufacturer Part NumberBU508AFManufacturerSTMicroelectronicsCategoryDiscrete Semiconductor ProductsTransistors - Bipolar (BJT) - SinglePackageISOWATT218FXSeries-Transistor TypeNPNCurrent - Collector (Ic) (Max)8AVoltage - Collector Emitter Breakdown (Max)700VVce Saturation (Max) @ Ib, IcIV @ 1.6A, 4.5ACurrent - Collector Cutoff (Max)200µAPower - MaxSoWFrequency - Transition-Operating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseISOWATT218FX		
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Current - Collector (Ic) (Max)8AVoltage - Collector Emitter Breakdown (Max)700VVce Saturation (Max) @ Ib, Ic1V @ 1.6A, 4.5ACurrent - Collector Cutoff (Max)200µADC Current Gain (hFE) (Min) @ Ic, Vce10 @ 100mA, 5VPower - Max50WFrequency - Transition-Operating Temperature150°C (TJ)Mounting TypeThrough Hole	Series	-
Voltage - Collector Emitter Breakdown (Max)700VVce Saturation (Max) @ Ib, Ic1V @ 1.6A, 4.5ACurrent - Collector Cutoff (Max)200µADC Current Gain (hFE) (Min) @ Ic, Vce10 @ 100mA, 5VPower - Max50WFrequency - Transition-Operating Temperature150°C (TJ)Mounting TypeThrough Hole	Transistor Type	NPN
Vce Saturation (Max) @ Ib, IcIV @ 1.6A, 4.5ACurrent - Collector Cutoff (Max)200µADC Current Gain (hFE) (Min) @ Ic, Vce10 @ 100mA, 5VPower - Max50WFrequency - Transition-Operating Temperature150°C (TJ)Mounting TypeThrough Hole	Current - Collector (Ic) (Max)	8A
Current - Collector Cutoff (Max)200μADC Current Gain (hFE) (Min) @ Ic, Vce10 @ 100mA, 5VPower - Max50WFrequency - Transition-Operating Temperature150°C (TJ)Mounting TypeThrough Hole	Voltage - Collector Emitter Breakdown (Max)	700V
DC Current Gain (hFE) (Min) @ Ic, Vce10 @ 100mA, 5VPower - Max50WFrequency - Transition-Operating Temperature150°C (TJ)Mounting TypeThrough Hole	Vce Saturation (Max) @ Ib, Ic	1V @ 1.6A, 4.5A
Power - Max50WFrequency - Transition-Operating Temperature150°C (TJ)Mounting TypeThrough Hole	Current - Collector Cutoff (Max)	200μΑ
Frequency - Transition-Operating Temperature150°C (TJ)Mounting TypeThrough Hole	DC Current Gain (hFE) (Min) @ Ic, Vce	10 @ 100mA, 5V
Operating Temperature150°C (TJ)Mounting TypeThrough Hole	Power - Max	50W
Mounting Type Through Hole	Frequency - Transition	-
	Operating Temperature	150°C (TJ)
Package / Case ISOWATT218FX	Mounting Type	Through Hole
	Package / Case	ISOWATT218FX
Supplier Device Package ISOWATT-218FX	Supplier Device Package	ISOWATT-218FX
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BU508AF Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE SUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.



If you have any question about BU508AF, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com